# **General Purpose Transistors**

**PNP Silicon** 

# BC856B, BC857B, BC858A

These transistors are designed for general purpose amplifier applications. They are housed in the SC-70/SOT-323 which is designed for low power surface mount applications.

#### **Features**

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

# **MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC856 BC857 BC858	V <sub>CEO</sub>	-65 -45 -30	V
Collector-Base Voltage BC856 BC857 BC858	V <sub>CBO</sub>	-80 -50 -30	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current - Continuous	I <sub>C</sub>	-100	mAdc
Collector Current - Peak (1 ms pulse)	I <sub>CM</sub>	-130	mA

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T <sub>A</sub> = 25°C	P <sub>D</sub>	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	883	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

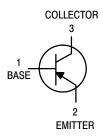
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.



# ON Semiconductor®

## www.onsemi.com





SC-70/SOT-323 CASE 419 STYLE 3

## **MARKING DIAGRAM**



XX = Specific Device Code

M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)
\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

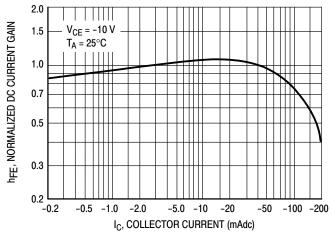
See detailed ordering and shipping information on page 5 of this data sheet.

1

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS				•	
Collector – Emitter Breakdown Voltage BC856 (I <sub>C</sub> = -10 mA) BC857 BC858	V <sub>(BR)CEO</sub>	-65 -45 -30	- - -	- - -	V
	V <sub>(BR)</sub> CES	-80 -50 -30	_ _ _	- - -	V
Collector – Base Breakdown Voltage BC856 (I <sub>C</sub> = -10 μA) BC857 BC858	V <sub>(BR)</sub> CBO	-80 -50 -30	- - -	- - -	V
	V <sub>(BR)EBO</sub>	-5.0 -5.0 -5.0	- - -	- - -	V
Collector Cutoff Current ( $V_{CB} = -30 \text{ V}$ ) ( $V_{CB} = -30 \text{ V}$ , $T_A = 150^{\circ}\text{C}$ )	I <sub>CBO</sub>	- -	- -	-15 -4.0	nA μA
ON CHARACTERISTICS					
DC Current Gain BC856A, BC585A BC856B, BC857B, BC858B BC857C	h <sub>FE</sub>	- - -	90 150 270	- - -	ı
$(I_C = -2.0 \text{ mA}, V_{CE} = -5.0 \text{ V})$ BC856A, BC858A BC856B, BC857B, BC858B BC857C		125 220 420	180 290 520	250 475 800	
Collector – Emitter Saturation Voltage ( $I_C = -10$ mA, $I_B = -0.5$ mA) ( $I_C = -100$ mA, $I_B = -5.0$ mA)	V <sub>CE(sat)</sub>	- -	- -	-0.3 -0.65	V
Base – Emitter Saturation Voltage ( $I_C = -10$ mA, $I_B = -0.5$ mA) ( $I_C = -100$ mA, $I_B = -5.0$ mA)	V <sub>BE(sat)</sub>	- -	-0.7 -0.9	- -	V
Base – Emitter On Voltage ( $I_C$ = -2.0 mA, $V_{CE}$ = -5.0 V) ( $I_C$ = -10 mA, $V_{CE}$ = -5.0 V)	V <sub>BE(on)</sub>	-0.6 -	_ _	-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product ( $I_C = -10$ mA, $V_{CE} = -5.0$ Vdc, $f = 100$ MHz)	f <sub>T</sub>	100	_	_	MHz
Output Capacitance (V <sub>CB</sub> = -10 V, f = 1.0 MHz)	C <sub>ob</sub>	_	_	4.5	pF
Noise Figure (I <sub>C</sub> = $-0.2$ mA, V <sub>CE</sub> = $-5.0$ Vdc, R <sub>S</sub> = $2.0$ k $\Omega$ , f = $1.0$ kHz, BW = $200$ Hz)	NF	-	_	10	dB

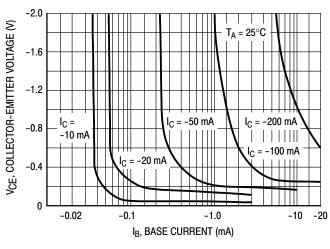
## BC857/BC858



-1.0 -0.9 T<sub>A</sub> = 25°C  $V_{BE(sat)} @ I_C/I_B = 10$ -0.8 V, VOLTAGE (VOLTS) -0.7  $V_{BE(on)}$  @  $V_{CE} = -10 \text{ V}$ -0.6 -0.5 -0.4 -0.3 -0.2  $V_{CE(sat)} @ I_C/I_B = 10$ -0.1 -0.2 -2.0 -0.1 -5.0 -50 -100 IC, COLLECTOR CURRENT (mAdc)

Figure 1. Normalized DC Current Gain

Figure 2. "Saturation" and "On" Voltages



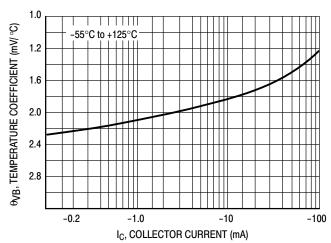
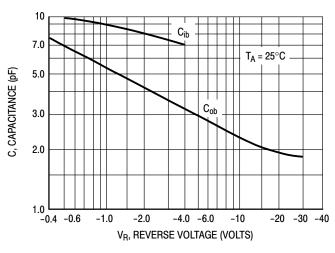


Figure 3. Collector Saturation Region

Figure 4. Base-Emitter Temperature Coefficient



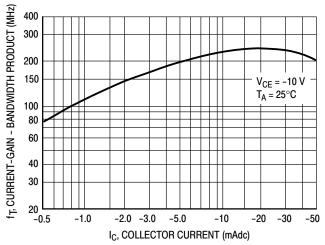


Figure 5. Capacitances

Figure 6. Current-Gain - Bandwidth Product

## **BC856**

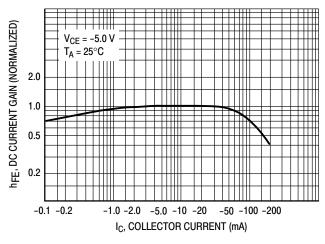


Figure 7. DC Current Gain

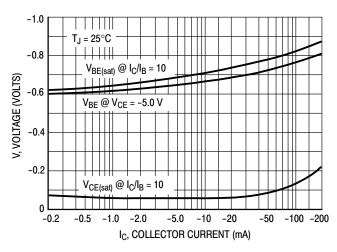


Figure 8. "On" Voltage

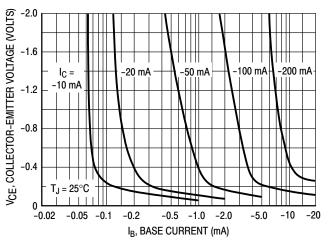


Figure 9. Collector Saturation Region

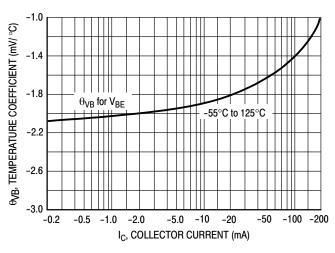


Figure 10. Base-Emitter Temperature Coefficient

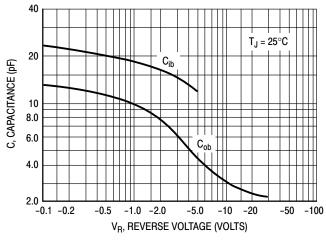


Figure 11. Capacitance

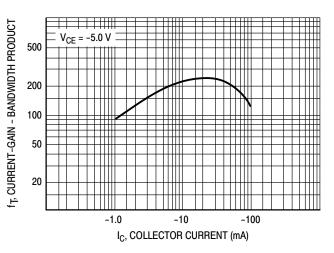


Figure 12. Current-Gain - Bandwidth Product

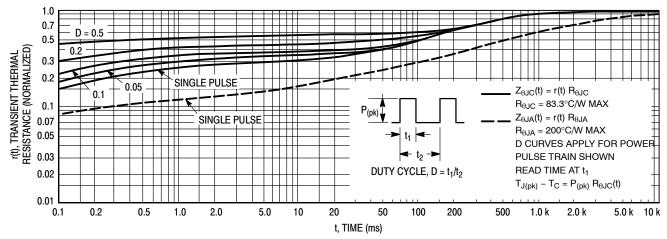


Figure 13. Thermal Response

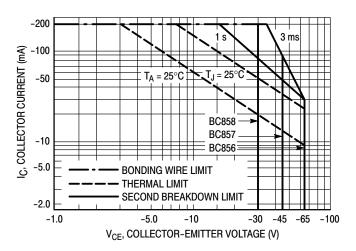


Figure 14. Active Region Safe Operating Area

The safe operating area curves indicate  $I_C$ – $V_{CE}$  limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon  $T_{J(pk)} = 150^{\circ} C$ ;  $T_{C}$  or  $T_{A}$  is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^{\circ} C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

#### **ORDERING INFORMATION**

Device	Marking	Package	Shipping <sup>†</sup>	
BC856BWT1G	3B	SC-70/SOT-323	3,000 / Tape & Reel	
SBC856BWT1G*	ЭБ	(Pb-Free)	3,000 / Tape & Reel	
BC857BWT1G	3F	SC-70/SOT-323	3,000 / Tape & Reel	
SBC857BWT1G*	31	(Pb-Free)		
BC857CWT1G	3G	SC-70/SOT-323	3,000 / Tape & Reel	
NSVBC857CWT1G*	30	(Pb-Free)	3,000 / Tape & Neer	
BC858AWT1G	3J	SC-70/SOT-323 (Pb-Free)	3,000 / Tape & Reel	
BC858BWT1G	зК	SC-70/SOT-323 (Pb-Free)	3,000 / Tape & Reel	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.





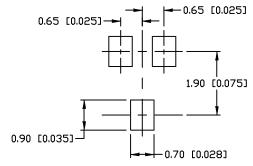
SC-70 (SOT-323) CASE 419 ISSUE P

**DATE 07 OCT 2021** 

#### NOTES:

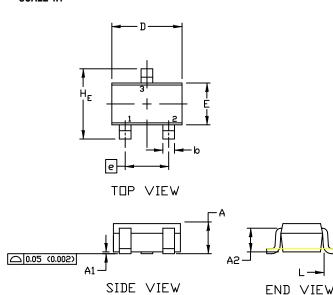
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 BS	C
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
Ε	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BS	C
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095
				`		



For additional information on our Pb-Free strategy and soldering details, please download the IIN Semiconductor Soldering and Mounting Techniques Reference Manual, SILDERRM/D.

SOLDERING FOOTPRINT



# GENERIC MARKING DIAGRAM



XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	2. CATHODE
3. COLLECTOR	3. COLLECTOR	3. DRAIN	3. CATHODE-ANODE	3. ANODE-CATHODE	3. CATHODE

DOCUMENT NUMBER:	98ASB42819B	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative